# Sol-Gel derived tungsten oxide thin films deposited by spin coating technique using tungsten powder as starting material

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#### Abstract

Tungsten oxide (WO<sub>3</sub>) thin films were deposited onto F-doped tin oxide (FTO) substrates using spin coating technique. The starting precursor for tungsten source was prepared from tungsten powder (Aldrich 12 micron; 99.9%) dissolved in 15% hydrogen peroxide. The coated films were annealed in ambient air for 2 hours at different annealing temperatures ranging from 200-500 °C. The differential-thermogravimetric measurement on the starting stock solution was performed to study its thermal property and decomposition/transformation. It was informed that the phase transformation and tungsten oxide crystallization was initiated at the temperature beyond 300 °C. X-ray diffraction was employed to characterize structural properties of the prepared films. The relevant chemical bonding of the films was investigated by fourier transform infrared spectroscopy. The optical and electrochromic properties of thin films were monitored by mean of UV-Vis spectroscopy technique. Further results and discussed will be represented in details.

Keywords: Sol-gel, tungten oxide, spin coating, annealing temperature

#### 1. Introduction

Due to its outstanding optical properties, tungsten oxide (WO<sub>3</sub>) is one of the most extensively used materials for practical application such as smart windows, electrochromic windows, switchable devices and sensors [1]. In particular, tungsten oxide has been widely applied as a key active material for smart windows, which possess variable light transmission characteristics and may be useful for applications in building or car industries. Up to now, several techniques have been notified to be applicable for metal-oxide thin film coatings including sputtering [2], chemical vapor deposition [3], electron beam deposition [4], pulsed spray pyrolysis [5] and spin coating [6]. Sol-gel spin coating has significant advantages among the other including cost-effective experimental arrangement, ease of adding dopant, high homogeneity, low process temperature, reproducibility and mass production capability for uniform large area coatings, Meanwhile, many effort have been devoted to improve the optical properties of tungsten oxide films by doping with transition metals such as Ti, V, Co, Fe, Zn [7]. Nevertheless, based on our recent knowledge a limitation of literatures focusing on the preparation and characterization of WO<sub>3</sub> thin films are available. In this work, WO<sub>3</sub> optical thin films were coated onto F-doped  $SnO_2$  (FTO) substrates by spin coating technique. The structural properties of WO<sub>3</sub> thin films were characterized by X-ray diffraction technique (XRD). The relevant optical properties (color or bleach) were extracted from transmission spectra obtained by UV-vis spectroscopy.



Fig. 1. TG-DTA curves of as-prepared WO<sub>3</sub> powder

### 2. Experimental details

The WO<sub>3</sub> thin films were deposited by sol-gel spin coating. The starting precursor was prepared from tungsten powder (Aldrich 12 micron; 99.9%) dissolved in 15% hydrogen peroxide. The dissolution was kept at 10-15 °C which finally resulted to pale yellow solution. WO<sub>3</sub> electrochromic thin films were deposited onto FTO (thickness~400 nm) conducting substrates with sheet resistance of 15  $\Omega$ /m. The sol-gel solution was coated by a spinner at frequency of 2000 rpm. After each coating, the sample was baked at 100 °C for 5 min and finally annealed at different temperatures from 200-500 °C in ambient air for 2 h. The effect of annealing temperature on structural properties of the films were characterized by X-ray diffraction (XRD). The optical properties of the films were investigated using UV-Vis spectrophotometer (Thermo Electron Corporation Heliosa).

#### 3. Results and discussion

The differential-thermogravimetric (TG/DTG) curves of tungsten powder stock solution were carried and the corresponding result is illustrated in Fig. 1. The first shown slight weight loss at temperature 74 °C attributes to evaporation of physically-adsorbed water and molecules, decomposition of peroxo groups and the combustion of organic species. The second peak at 280 °C is ascribed to burn out of organic species which starting point of crystallization of WO<sub>3</sub> [8].

The X-ray diffraction patterns of WO<sub>3</sub> thin films with difference annealing temperatures on FTO substrates are illustrated in Fig.2. The XRD patterns of the films annealed at 200 and 300 °C do not exhibit characteristic peaks of WO<sub>3</sub>, indicating that the structure of the films deposited at this temperature are amorphous phase. With increasing deposition temperature elevated to 400 °C, the noticeable diffraction peak position at  $2\theta$  values of 24.14° corresponding to (200) orientation plane of monoclinic WO<sub>3</sub> is clearly observed, indicating



Fig. 2. XRD patterns of WO<sub>3</sub> thin films annealed at different temperatures.

the formation of monoclinic structure of WO<sub>3</sub> films after annealing process. Further increasing temperature to 500 °C results to the intensity of the WO<sub>3</sub> (200) peak becomes stronger and the existence of (002) orientation plane peak at  $2\theta$  values of 23.1° which reflect to as annealing temperature arise suggesting that crystallinity of the film significantly improves at higher annealing temperature. The other diffraction peaks identified at 26.5°, 33.7°, 37.7°, 51.5° correspond to (110), (101), (200), (211) orientation plane for FTO substrate [9]. With increasing deposition temperature elevated to 500 °C observed in XRD patterns at  $2\theta$ =24.14° and 28.64° planes (002), (020), (210), (112) indicating peak of WO<sub>3</sub>[10].



Fig. 3. FTIR spectra of WO3 thin films with annealing temperature at 300 °C and 500 °C.



**Fig. 4.** High resolution X-ray photoelectron of WO<sub>3</sub> thin films annealed at 500 °C: (a) survey, (b) W4f, (c) O1s

The vibrational modes of the chemical groups in the WO<sub>3</sub> at different temperature were examined by FTIR spectroscopy. Fig. 3 shows the FTIR spectra of WO<sub>3</sub> thin films with different annealing temperatures at 300 °C and 500 °C in in the wavelength range 500-4000 cm<sup>-1</sup>. The film with annealing temperature at 300 °C shows the peaks situate at 661, 797 and 948 cm<sup>-1</sup> are ascribed to the vibration bonding of W-O, W-O and W=O stretching mode, respectively. In addition, the intensity of W=O bonding significantly increased when annealing temperature raised to 500 °C. This result implies that the number of W=O increases with the annealing temperature [12]. XRD and FTIR results indicate that the annealing temperature can be improved the quality of the films.

The survey spectrum of XPS shows three peaks corresponding to tungsten, oxygen and carbon based in the binding energy range 0-1200 eV, as shown in Fig. 4a. The fine spectrum of W consisting of spilt double peaks is shown in Fig. 4b. Two major peaks are well separated without any shoulders at ca. 35.6 and 37.6 eV are ascribed to W4f<sub>7/2</sub> and W4f<sub>5/2</sub>, respectively. This result suggests that the W<sup>6+</sup> ions are obtained on the surface of a film. The O1s peaks at 530.17 and 532.15 eV are assigned to the O<sup>2-</sup> and O-H phases at the surface of WO<sub>3</sub> thin films (as shows in Fig. 4c) [13].

The electrochromic experiment of WO<sub>3</sub> films prepared by spin coating method using H<sub>2</sub>SO<sub>4</sub> concentration of 0.01 M as an electrolyte. Electric field + 3V for 30 s. The light transmission of three states consist of as-deposited state, color state and bleach state are shown in Fig. 5. From the results, the as-deposited film shows the highest transmittance. After applied electric field, the film are obtained to dark-blue color at colored state owning to the ion insertion reduced some W<sup>6+</sup> states to W<sup>5+</sup> states. On the contrary, the ions ejection reduced some W<sup>5+</sup> states to W<sup>6+</sup> states lead to the film change from colored to bleach state. The ions transport process according to the following electrochemical reaction [14]:

$$WO_3 + xH^+ + xe^- \leftrightarrow H_xWO_3$$
 (1)



Fig. 5. Transmittance spectra of WO3 thin films annealed at 500 °C with different colored states.

## 4. Conclusion

In summary, the WO<sub>3</sub> films with monoclinic structure were successfully deposited via solgel spin coating technique using annealing temperature at 500 °C. FTIR spectra results show the peaks of W-O and W=O stretching mode. The XPS results indicate that the W<sup>6+</sup> ions are obtained on the surface of a film. The electrochromic result suggests that the colored state of WO<sub>3</sub> films can be transformed by injection/ejection of ions into the films which suitably as smart window.

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